

SMPS MOSFET

IRFB260NPbF

HEXFET® Power MOSFET

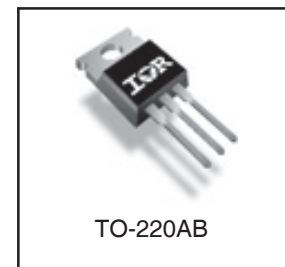
Applications

- High frequency DC-DC converters
- Lead-Free

V_{DSS}	R_{DS(on) max}	I_D
200V	0.040Ω	56A

Benefits

- Low Gate-to-Drain Charge to Reduce Switching Losses
- Fully Characterized Capacitance Including Effective C_{OSS} to Simplify Design, (See App. Note AN1001)
- Fully Characterized Avalanche Voltage and Current



Absolute Maximum Ratings

	Parameter	Max.	Units
I _D @ T _C = 25°C	Continuous Drain Current, V _{GS} @ 10V	56	A
I _D @ T _C = 100°C	Continuous Drain Current, V _{GS} @ 10V	40	
I _{DM}	Pulsed Drain Current ①	220	
P _D @ T _C = 25°C	Power Dissipation	380	W
	Linear Derating Factor	2.5	W/°C
V _{GS}	Gate-to-Source Voltage	± 20	V
dv/dt	Peak Diode Recovery dv/dt ②	10	V/ns
T _J	Operating Junction and	-55 to + 175	°C
T _{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds		
	Mounting torque, 6-32 or M3 screw	10 lbf•in (1.1N•m)	

Thermal Resistance

	Parameter	Typ.	Max.	Units
R _{θJC}	Junction-to-Case	—	0.40	°C/W
R _{θCS}	Case-to-Sink, Flat, Greased Surface	0.50	—	
R _{θJA}	Junction-to-Ambient	—	62	

Notes ① through ③ are on page 8

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